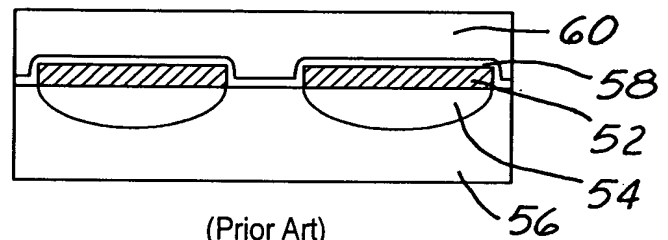


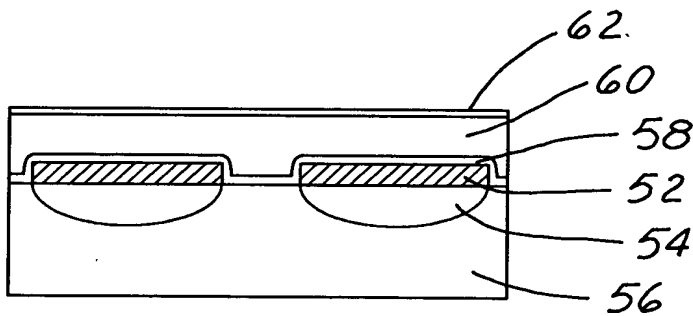
(Prior Art)

FIG. 2B



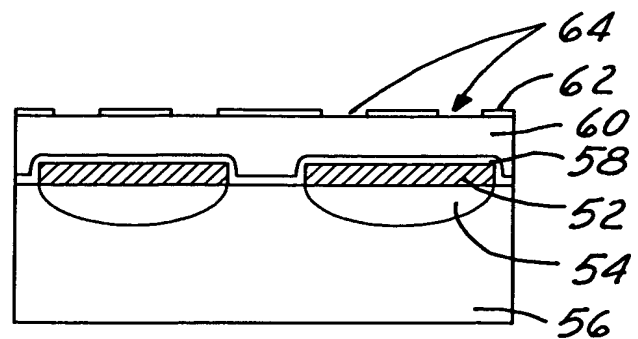
(Prior Art)

FIG. 2C



(Prior Art)

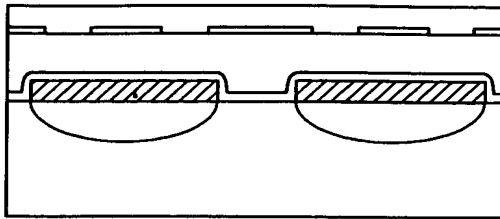
FIG. 2D



(Prior Art)

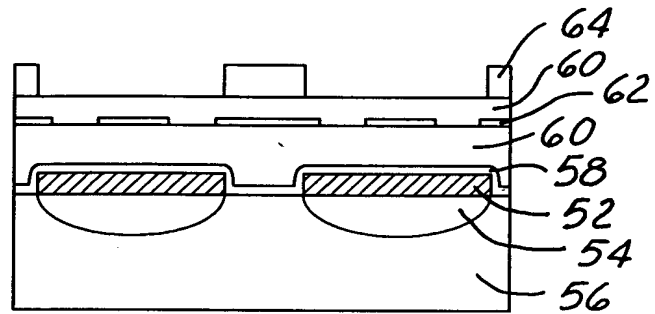
FIG. 2E

09941356-082901



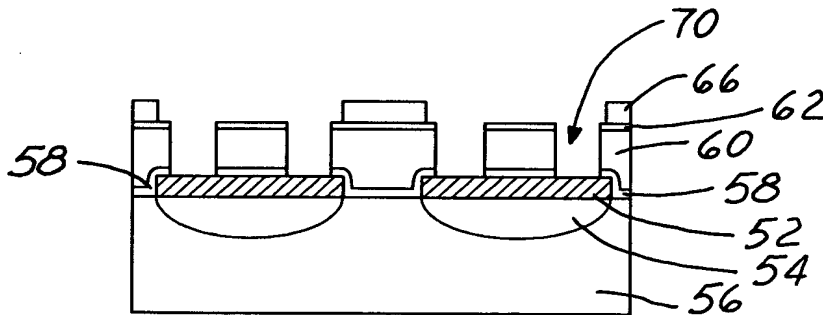
(Prior Art)

FIG. 2F



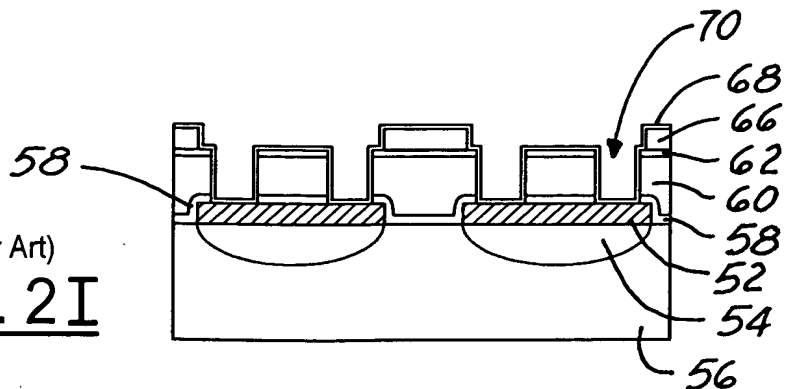
(Prior Art)

FIG. 2G



(Prior Art)

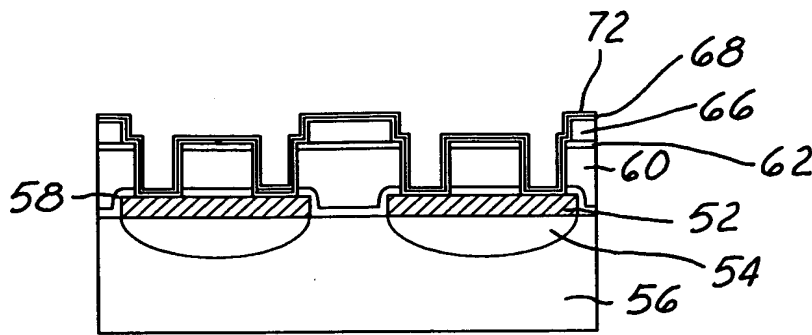
FIG. 2H



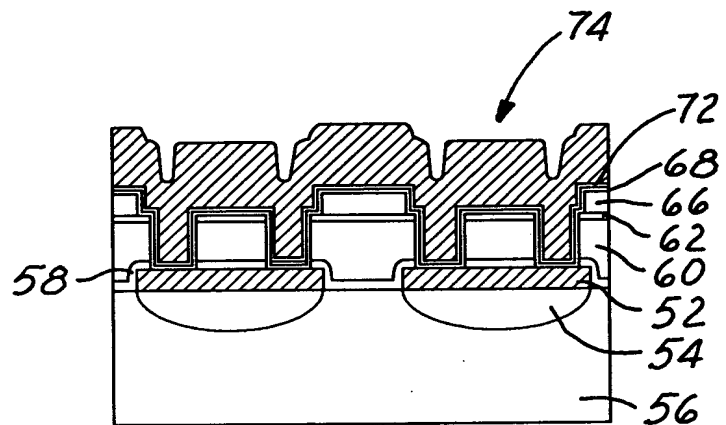
(Prior Art)

FIG. 2I

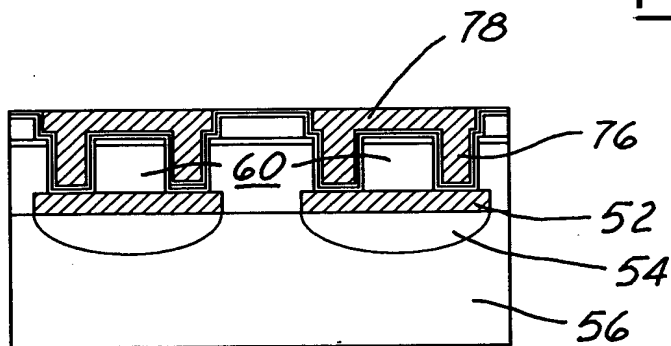
09941356-082901



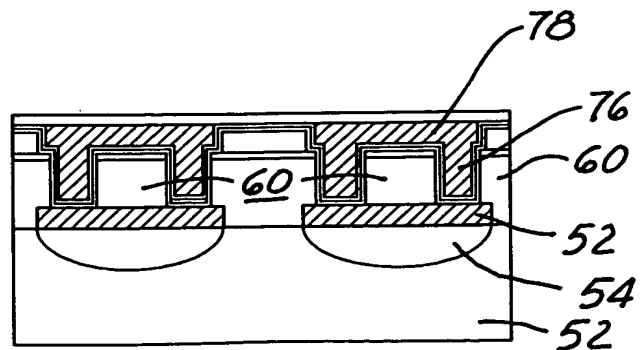
(Prior Art)
FIG. 2J



(Prior Art)
FIG. 2K

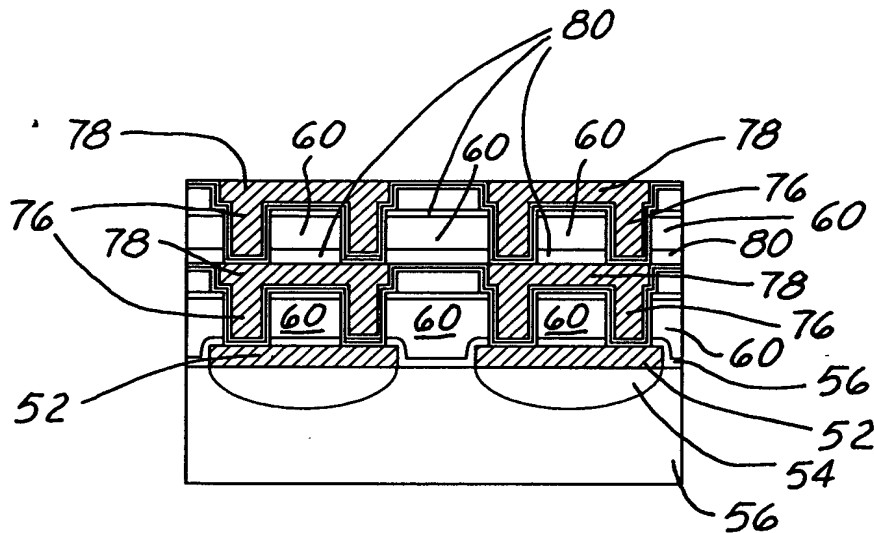


(Prior Art)
FIG. 2L



(Prior Art)
FIG. 2M

09441355-082901



(Prior Art)

FIG. 2N

Providing or Forming a
Semiconductor Device having
Two Metal Interconnects and
a Low Dielectric Constant Material
There Between



Etching the Low Dielectric
Constant Material with an
Aqueous Solution Including
HF and HCL



Analyzing the Etched Device
with a Scanning Electron
Microscope

FIG. 3

09041356 082901
T06280 95ET4660